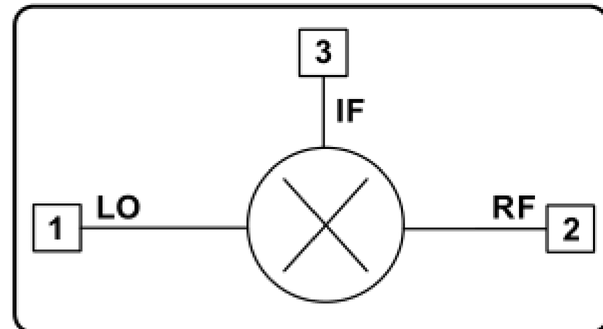
Features

- Passive Type: No DC biasing required
- RF Frequency: 1.8-5GHz
- IF Bandwidth: DC-3GHz
- Conversion Loss: 8 dB
- LO/RF Isolation: 35 dB
- P1dB: +13 dBm
- Die Size: 1.45 x 1.45 x 0.1 mm

Functional Block Diagram



Typical Applications

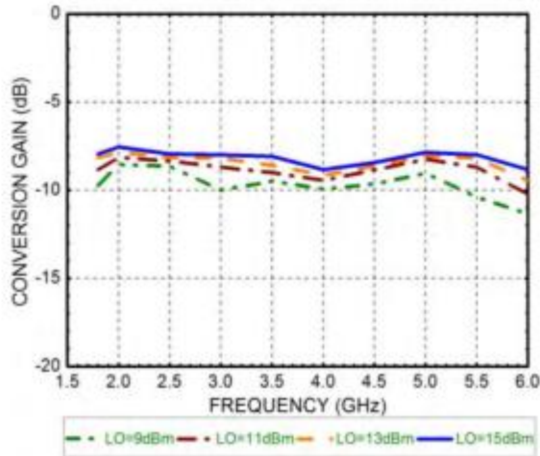
- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

Electrical Specifications

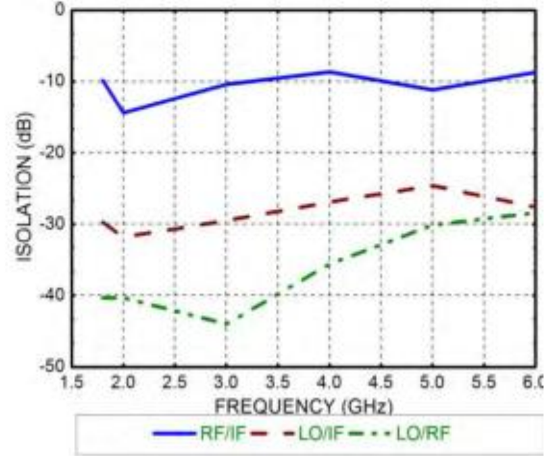
TA = +25ºC, IF = 100MHz, LO = +13dBm

Parameters	Min.	Typ.	Max.	Units
RF Frequency (RF/LO)		1.8-5		GHz
IF Frequency (IF)		DC-3		GHz
Conversion Loss		8		dB
Isolation “LO to RF”		35		dB
Isolation “LO to IF”		30		dB
Isolation “RF to IF”		10		dB
Input 1dB Compression		13		dBm
Input Third Order Intercept (IIP3)		20		dBm

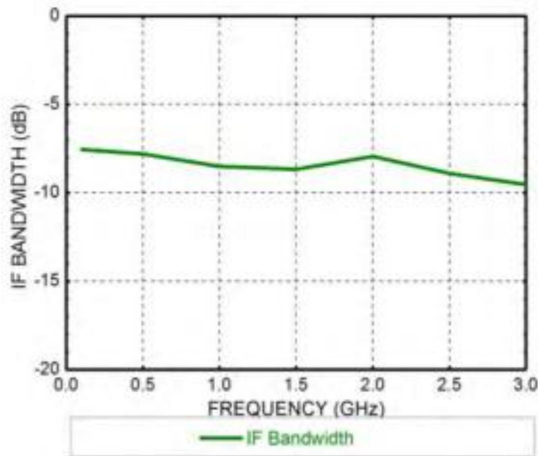
Conversion Gain vs. LO Driver



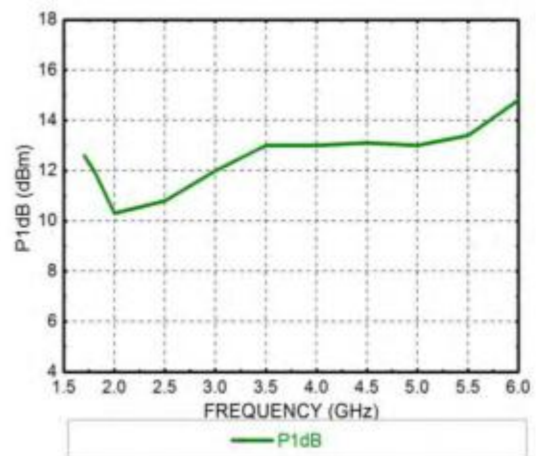
Isolation



IF Bandwidth

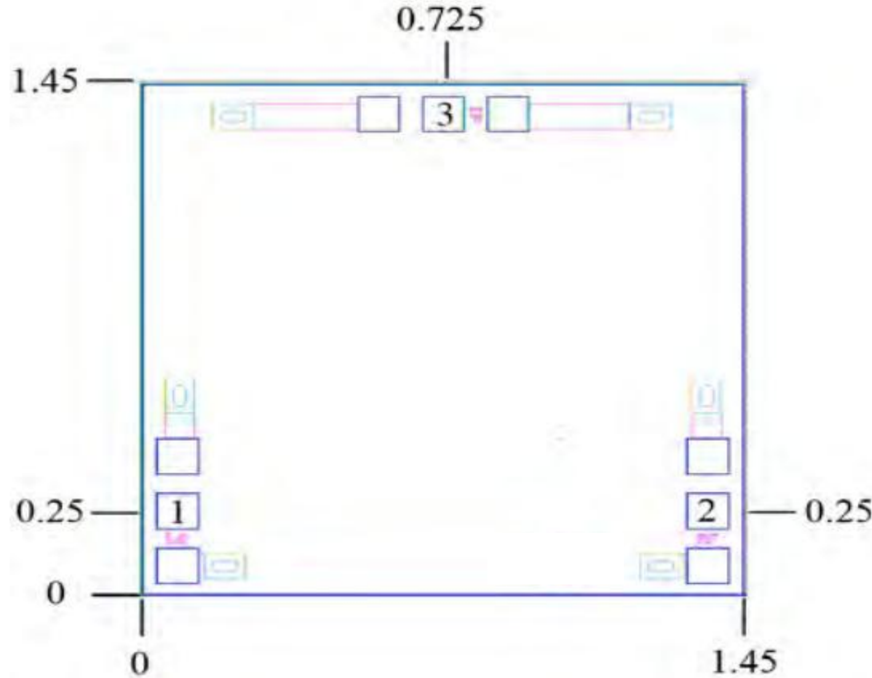


Input P1dB



Outline Drawing:

All Dimensions in mm



Pad Description

Pad Number	Function	Description
1	LO	DC coupling 50Ω Impedance
2	RF	DC coupling 50Ω Impedance
3	IF	DC coupling 50Ω Impedance
Die bottom	GND	Die bottom must be connected to RF/DC ground.

Notes:
1. Die thickness: 100um
2. Typical bond pad is 100*100 μm²
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die is grounded
6. No connection required for unlabeled bond pads

Maximum Ratings:
1. RF/IF input power: +24dBm
2. Local oscillator drive power: +24dBm
3. Storage temperature: -65℃ to +150℃
4. Operating temperature: -55℃ to +85℃